

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	@pn="3958040"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 08:59
S2	1	@pn="5493470"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:02
S3	1	@pn="5631428"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:03
S4	3	"6670538"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:03
S5	2	(chase and logsdon and kingery).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:22
S6	1239	LOCOS and MEMS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:23
S7	196	S6 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:38
S8	275	438/117.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:46

S9	219	S8 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:46
S10	243	438/456.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:59
S11	226	S10 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 12:59
S12	3860	438/694.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:17
S13	3708	S12 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 13:24
S15	108	S13 and ((silicon adj nitride) ("Si. sub.3N.sub.4")) and ((silicon adj oxide) ("SiO.sub.2")) same (back rear backside bottom opposite)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 13:10
S16	809	438/787.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 14:17
S17	749	S16 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 16:10

S18	26	LOCOS near8 (back rear opposite bottom) near2 (wafer substrate die chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 13:34
S19	25	S18 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 13:36
S20	1428	((silicon adj nitride) ("si.sub.3N.sub.4") ("si.sub.3" adj "N.sub.4")) same ((silicon adj oxide) ("sio.sub.2") (silicon adj dioxide)) same (back rear opposite bottom) near2 (wafer substrate die chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 13:35
S21	1264	S20 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 13:41
S22	73	((silicon adj nitride) ("si.sub.3N.sub.4") ("si.sub.3" adj "N.sub.4")) same (back rear opposite bottom) near2 (wafer substrate die chip) and ((silicon adj oxide) ("sio.sub.2") (silicon adj dioxide)) near2 both	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 13:41
S23	3	((silicon adj nitride) ("si.sub.3N.sub.4") ("si.sub.3" adj "N.sub.4")) same (back rear opposite bottom) near2 (wafer substrate die chip) and ((silicon adj oxide) ("sio.sub.2") (silicon adj dioxide)) near2 opposite\$2 near2 (side surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 13:41
S24	23	((silicon adj nitride) ("si.sub.3N.sub.4") ("si.sub.3" adj "N.sub.4")) same (back rear opposite bottom) near2 (wafer substrate die chip) and ((silicon adj oxide) ("sio.sub.2") (silicon adj dioxide)) near2 (opposite\$2 both) near2 (side surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 13:41
S25	21	S24 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 14:17

S26	457	438/791.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 14:17
S27	418	S26 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 16:13
S28	588	257/684.ccls. and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 14:28
S29	1	257/684.ccls. and @ad<"20040401" and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 14:48
S30	2	257/678.ccls. and @ad<"20040401" and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:15
S31	2293	257/678.ccls. and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:15
S32	111	438/698.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 09:50
S33	109	S32 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:23

S34	210	438/759.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:23
S35	109	S33 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:43
S36	61	((silicon adj nitride) ("Si.sub.3N. sub.4") ("Si.sub.3" adj "N.sub.4")) near2 mask and ((silicon adj oxide) (silicon adj dioxide) ("SiO.sub.2") oxide) adj mask and through adj hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:50
S37	38	S36 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:50
S38	134	((silicon adj nitride) ("Si.sub.3N. sub.4") ("Si.sub.3" adj "N.sub.4")) near2 mask and ((silicon adj oxide) (silicon adj dioxide) ("SiO.sub.2") oxide) adj mask and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:50
S39	109	S38 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:50
S40	101	S39 not S37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 15:50
S41	41	S17 and through adj hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 16:12

S42	5	S41 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 16:12
S43	318	S17 and via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 16:12
S44	35	S43 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 16:12
S45	57	S27 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 16:14
S46	8	wood.in. and ridley.in. and higashi.in. and honeywell.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 11:56
S47	785	"438"/\$.ccls. and oxide near5 ((upper near2 lower) both two) adj (surface plane side)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 11:58
S48	1017	"438"/\$.ccls. and oxide near5 ((upper near2 lower) opposite both two) adj (surface plane side)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 12:00
S49	52	S48 and encapsulat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 12:00

S50	45	S49 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 13:27
S51	494	S48 and silicon adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 13:27
S52	443	S51 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 13:38
S53	109	S52 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 13:28
S54	107	S53 not S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 13:28
S55	2061	((silicon adj nitride) ("si.sub.3N.sub.4") ("si.sub.3" adj "N.sub.4")) and ((silicon adj oxide) ("sio.sub.2") (silicon adj dioxide)) near8 (back rear opposite bottom both two (upper and lower)) near2 (wafer substrate die chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 13:37
S56	541	((silicon adj nitride) ("si.sub.3N.sub.4") ("si.sub.3" adj "N.sub.4")) and ((silicon adj oxide) ("sio.sub.2") (silicon adj dioxide)) near3 (back rear opposite bottom both two (upper and lower)) near2 (wafer substrate die chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 14:50
S57	500	S56 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 13:38

S58	1107	((silicon adj oxide) ("sio.sub.2") (silicon adj dioxide)) near3 (back rear opposite bottom both two (upper and lower)) near2 (wafer substrate die chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 14:51
S59	1033	S58 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 14:51
S60	95	S59 and through adj hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 14:59
S61	38	S60 not S57	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 14:53
S62	63	S59 and local\$4 adj (oxidation oxide oxidizing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 15:01
S63	63	S62 not S61	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 15:00
S64	10	S62 not S57	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 15:01
S65	24	S59 and selective adj (oxidation oxide oxidizing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 15:01

S66	5	S65 not S57	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 15:01
S67	5	S66 not S62	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 15:01
S68	1167	438/106.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:54
S69	981	S68 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:01
S70	1649	438/689.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:01
S71	1182	438/753.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:01
S72	980	S71 and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:08
S73	32	S71 and @ad<"20040401" and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:08
S74	0	("6723250").URPN.	USPAT	OR	ON	2005/12/06 10:28

S75	13	("4542650" "4957592" "4994141" "4996627" "5096791" "5131978" "5387316" "5389198" "5711891" "5738757" "5762813" "5804090" "6033997").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 10:28
S76	37	438/756.ccls. and LOCOS and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 16:04
S77	66	438/724.ccls. and LOCOS and @ad<"20040401"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 16:04
S78	1	@pn="6913701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 08:59